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PATENT Attorney Docket No. 401479/AOYAMA

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:

IZUO et al.

Art Unit: Unknown

Application No. Unknown

Examiner: Unknown

Filed: December 11, 2001

For:

ELECTROCHEMICAL ETCHING METHOD AND APPARATUS AND PRODUCT MANUFACTURED

THEREBY

PRELIMINARY AMENDMENT

Commissioner for Patents Washington, D.C. 20231

Dear Sir:

Prior to the examination of the above-identified patent application, please enter the following amendments and consider the following remarks.

IN THE DRAWINGS:

The Examiner is requested to approve the changes to Figure 10 as indicated in the attached Request for Approval of Drawing Amendments.

IN THE SPECIFICATION:

Replace the paragraph beginning at page 1, line 5 with:

The present invention relates to an electrochemical etching method and apparatus. In particular, the present invention relates to a method and apparatus in which an n-type silicon substrate is exposed at one surface to an electrolyte and at an opposite surface to light, so that a pore (hole) or a trench (groove) of a certain size and shape is formed in the substrate as an etching current flowing in the substrate is controlled by the light. Also, the present invention relates to a product, e.g., a semiconductor device, made by the use of the electrochemical etching method. It is to be understood that the present invention is preferably applicable to a method and apparatus for electrochemical etching for the formation of pores or trenches